Method for the double-side polishing of a semiconductor wafer

Abstract

The invention relates to a method for the double-side polishing of a semiconductor wafer, wherein the surfaces of the polishing pads are in each case interrupted by at least one channel-shaped depression running spirally from the center to the edge. By means of polishing agent being supplied on both sides, a locally individually adaptable quantity of polishing agent and a modified carrier plate, an optimized polishing agent distribution is achieved particularly in the case of semiconductor wafers having a diameter of 450 mm.

Fig. 1d